L Number		Search Text	DB	Time stamp
1	652	257/415.ccls.	USPAT;	2003/11/14 14:05
1 1			US-PGPUB;	1
			EPO; JPO; DERWENT;	1
1 1			IBM TDB	1
2	585	257/419.ccls.	USPAT;	2003/11/14 14:05
1 - 1			US-PGPUB;	
į į			EPO; JPO;	(
)			DERWENT:	1
			TBM TDB	
3	38	257/424.ccls.	USPAT;	2003/11/14 14:05
			US-PGPUB;	1
i l			EPO; JPO;	
			DERWENT;	1
ĺ	161	257 (2541)	IBM_TDB	00000100105 15 11
-	101	257/254.ccls.	USPAT;	2003/02/05 16:14
]			US-PGPUB; EPO; JPO;	1
}			DERWENT;	
			IBM TDB	1
-	9	(257/254.ccls. and (gate near3 oxide)) and	USPAT;	2003/02/05 16:12
		acceleration	US-PGPUB;	1, 12, 11 10112
			EPO; JPO;	
			DERWENT;	
)			IBM_TDB	
! -	2	((257/254.ccls. and (gate near3 oxide))	USPAT;	2003/02/05 16:12
1		and acceleration) and spring	US-PGPUB;	
1			EPO; JPO;	
1			DERWENT;	1
	10	017/05/	TBM_TDB	
[-]	10	257/254.ccls. and acceleration and spring	USPAT;	2003/02/05 16:15
i l			US-PGPUB; EPO; JPO;	I .
l í			DERWENT;	
i l			TBM TDB	ł.
[-	8	(257/254.ccls, and acceleration and	USPAT;	2003/02/05 16:19
!	- 10	spring) not ((257/254.ccls. and (gate	US-PGPUB:	
1		near3 oxide)) and acceleration)	EPO; JPO;	1
1			DERWENT;	
			IBM_TDB	1
-	12153	acceleration same switch	USPAT;	2003/07/30 14:48
			US-PGPUB;	1
1			EPO; JPO;	
			DERWENT;	1
1	21	(acceleration same switch) and ((gate	IBM_TDB USPAT;	2003/11/12 18:45
i .	21	near5 (oxide or insulator)) and (drain or	US-PGPUB;	2003/11/:2 18:45
		source))	EPO; JPO;	1
			DERWENT;	Į.
[]			IBM TDB	1
-	11	((acceleration same switch) and ((gate	USPAT;	2003/02/05 16:21
		near5 (oxide or insulator)) and (drain or	US-PGPUB;	1
1		source))) and spring	EPO; JPO;	1
			DERWENT;	
1			IBM TOB	
-	24	(acceleration same switch) and (gate near5	USPAT;	2003/02/05 16:22
)		(oxide or insulator))	US-PGPUB;	
			EPO; JPO;	1
			DERWENT; IBM TDB	1
	11	((acceleration same switch) and (gate	USPAT;	2003/02/05 16:31
	4.1	near5 (oxide or insulator))) and spring	US-PGPUB;	2003/02/03 10:31
		(Or Insurator), , and Spirity	EPO; JPO;	
			DERWENT;	1
1			IBM TOB	
-	363	(acceleration same switch) and gate and	USPĀT;	2003/02/05 16:57
		drain	US-PGPUB;	
1	i		EPO; JPO;	
			DERWENT;	
			JBM_TDB	

	0 ((acceleration same switch) and gate and	USPAT;	72003/02/05 16:58
	drain) and source	US-PGPUB; EPO; JPO; DERWENT;	
_ 31	2 (((acceleration same switch) and gate and	IBM_TDB USPAT;	2003/02/05 16:59
	drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)))	US-PGPUB; EPO; JPO; DERWENT;	2003/02/03 10:33
-	0 (((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)))) and spring) not	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/02/05 17:44
	((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator))))	TBM TDB	
18	3 ((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate nearb (oxide or insulator)))) not (((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/05 17:52
- 16	<pre>near5 (oxide or insulator))) and spring) 0 257/254.ocls. not ((accoleration same switch) and (gate near5 (oxide or insulator)))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/05 17:53
- 1	5 (257/254.ccls. and (gate near3 oxide)) not ((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; JBM TDB	2003/02/05 17:53
-	US-5619050-\$ or US-5504356-\$ or US-5922212-\$ or US-6388299-\$ or US-5912427-\$).did.	USPAT	2003/02/06 13:00
-	5 (US-5619050-\$ or US-5504356-\$ or US-5922212-\$ or US-6388299-\$ or US-5812427-\$).did.	USPAT	2003/02/06 12:58
-	5 (US-5619050-\$ or US-5504356-\$ or US-5922212-\$ or US-6388299-\$ or US-5812427-\$).did.	USPAT	2003/02/06 12:58
-	1 ("5619050").PN.	USPAT	2003/02/06 12:59
-	1 ((US-5619050-\$ or US-5504356-\$ or US-5922212-\$ or US-6388299-\$ or US-5812427-\$).did.) and (silicon near dioxide)	USPAT	2003/02/06 13:03
-	1 ((US-5619050-\$ or US-5504356-\$ or US-5922212-\$ or US-6388299-\$ or US-5812427-\$).did.) and (silicon near dioxide)	USPAT	2003/02/06 13:03
- 1	3 ((acceleration same switch) and (gate noar5 (oxide or insulator)) not (((acceleration same switch) and (gate near5 (oxide or insulator))) and spring)	USPAT; US-PGPUB; EPO; JPO; DERWENT; 1BM TDB	2003/02/06 13:05
	O (((acceleration same switch) and (gate near5 (oxide or insulator)) not (((acceleration same switch) and (gate near5 (oxide or insulator)) and spring)) and (silicon near3 dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; JBM TDB	2003/02/06 13:05
- 1	257/254.ccts. and (gate near3 oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TOB	2003/02/06 13:05

-	4	(257/254.ccls. and (gato near3 oxide)) and (silicon near3 dioxide)	USPAT; US-PGPUB; EPO; JPO;	2003/07/30 15:29
-	129	((((acceleration same switch) and gate and	DERWENT; IBM_TDB USPAT;	2003/02/06 13:10
		drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)))) and spring	US-PGPUB; EPO; JPO; DERWENT;	
-	0	((((((acceleration same switch) and gate and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/02/06 13:11
-	1	insulator)))) and spring) and (silicon near3 oxide) (((((acceleration same switch) and gate	DERWENT; IBM_TDB USPAT;	2003/02/06 13:11
		and drain) and source) not ((acceleration same switch) and (gate near5 (oxide or insulator)))) and spring) and (silicon	US-PGPUB; EPO; JPO; DERWENT;	
-	238	noar3 dioxido) 73/514.36.ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/02/06 13:11
-	193	73/514.36.ccls. and (acceleration or	DERWENT; IBM_TDB USPAT;	2003/02/06 13:12
		prossure)	US-PGPUB; EPO; JPO; DERWENT;	
-	4	(73/514.36.ccls. and (acceleration or pressure)) and gate and (silicon near3 dioxide)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/02/06 13:12
-	2190	("5627397").FN. (acceleration same switch) and (semiconductor or ic or (integrated near2 circuit) or chip or die)	IBM TDB USPAT USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/02/06 14:34 2003/07/30 14:50
-	1458	((acceleration same switch) and (semiconductor or ic or (integrated near2 circuit) or chip or die)) and (source or drain)	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/12 18:34
-	167	257/254.ccls.	IBM_TDH USPAT; US-PGPUH; EPO; JPO;	2003/07/30 15:29
-	818	257/417.ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/07/30 15:29
-	243	257/418.ccls.	DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO;	2003/07/30 15:30
-	157	257/420.ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/11/14 14:05
	163	77/51/ 211	FPO; JPO; DERWENT; IBM TDB	2002/07/20 15 22
	103	73/514.21.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; 1BM_TDB	2003/07/30 15:30

Ţ-	1508	((acceleration same switch) and	USPAT;	2003/11/12 18:35
		(semiconductor or ic or (integrated near2	US-PGPUB;	
		circuit) or chip or die)) and (source or	EPO; JPO;	1
i		drain)	DERWENT;	l i
			IBM TDB	[]
-	26	(acceleration same switch) and ((gate	USPAT;	2003/11/12 18:45
(1	near5 (oxide or insulator)) and (drain or	US-PGPUB;	
		source))	EPO; JPO;	f I
1	(DERWENT;	
			IBM TDB	